





P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) Max	I _D T _A = +25°C
-12V	$31m\Omega$ @ V _{GS} = -4.5V	-5.2A
-12V	45mΩ @ V _{GS} = -2.5V	-4.3A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP1045UQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC converters
- **BLDC** motors
- Load switches

Mechanical Data

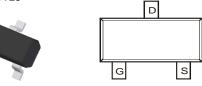
- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208@3
- Weight: 0.009 grams (Approximate)

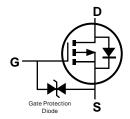




Top View

SOT23





Internal Schematic

Ordering Information (Note 4)

Orderskie Bort Number	Daekana	Packing		
Orderable Part Number	Package	Qty.	Carrier	
DMP1045UQ-7	SOT23	3,000	Tape & Reel	

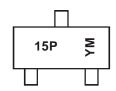
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

Pin Configuration

- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



15P = Product Type Marking Code YM or $\overline{Y}M$ = Date Code Marking Y or \overline{Y} = Year (ex: L = 2024) M = Month (ex: 9 = September)

Date Code Key

Year	2014	-	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	В	1	L	М	Ν	Р	R	S	Т	J	V	W
Mande								A	Sep	Oct	Nov	Dec
IVIONTO	ı .ıan	⊢en -	Mar	Δnr	I IVIAV	Jun	-1111	Aud	Seb	Oct	NOV	Dec
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	NOV	Dec



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-12	V		
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 5) Vgs = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	lο	-4.0 -3.1	А
Continuous Drain Current (Note 5) Vgs = -2.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	lο	-3.3 -2.6	А
Continuous Drain Current (Note 6) Vgs = -4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	lο	-5.2 -4.2	А
Continuous Drain Current (Note 6) V _{GS} = -2.5V	Steady State	T _A = +25°C T _A = +70°C	Ι _D	-4.3 -3.4	А
Maximum Continuous Body Diode Forward Current	Is	-2	A		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	(Note 6)		I _{DM}	-40	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	168	°C/W
Total Power Dissipation (Note 6)	PD	1.3	W
Thermal Resistance, Junction to Ambient (Note 6)	RθJA	99	°C/W
Thermal Resistance, Junction to Case (Note 6)	Rejc	14.8	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = ±25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	-12	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1.0	μΑ	V _{DS} = -12V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±10	μA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	-0.3	-0.55	-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
			26	31		VGS = -4.5V, ID = -4.0A	
Static Drain-Source On-Resistance	RDS(ON)	_	31	45	$m\Omega$	Vgs = -2.5V, ID = -3.5A	
			45	75		Vgs = -1.8V, ID = -2.7A	
Forward Transfer Admittance	Y _{fs}	_	12	_	S	V _{DS} = -5V, I _D = -4A	
Diode Forward Voltage	VsD	_	-0.6	_	V	V _G S = 0V, I _S = -1A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	1357	1	pF	101/1/	
Output Capacitance	Coss	_	504	-	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	235	-	pF	1 = 1.0WH12	
Gate Resistance	Rg	_	14.1	_	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz	
SWITCHING CHARACTERISTICS (Note 8)							
Total Gate Charge	Q_g	_	15.8	-	nC		
Gate-Source Charge	Qgs	_	2.0	_	nC	VGS = -4.5V, VDS = -10V, ID = -4A	
Gate-Drain Charge	Q_{gd}	_	3.9	-	nC		
Turn-On Delay Time	td(ON)	_	15.7	_	ns		
Turn-On Rise Time	t _R	_	23.3	_	ns	V _{DS} = -10V, V _{GS} = -4.5V,	
Turn-Off Delay Time	tD(OFF)	_	91.2	_	ns	$R_L = 2.5\Omega$, $R_G = 3.0\Omega$	
Turn-Off Fall Time	tF	_	106.9		ns		

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.



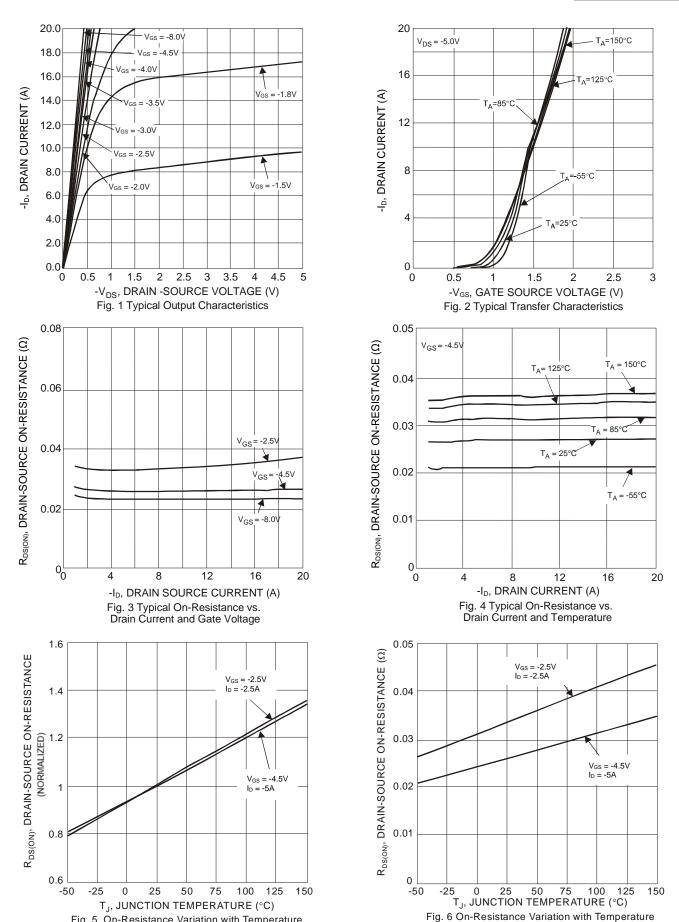


Fig. 5 On-Resistance Variation with Temperature



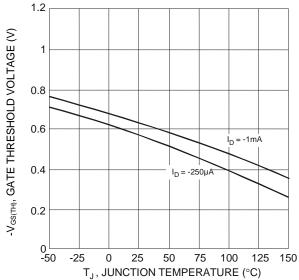


Fig. 7 Gate Threshold Variation vs. Junction Temperature

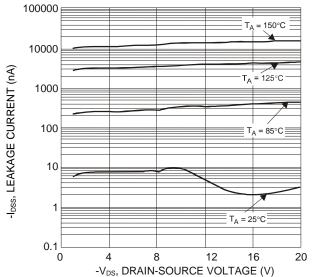


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage

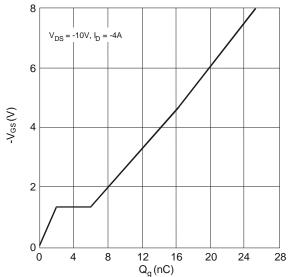
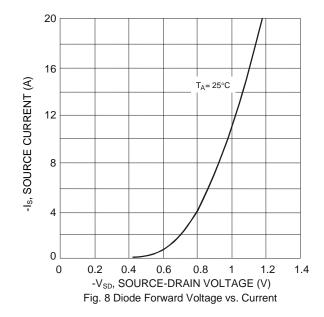
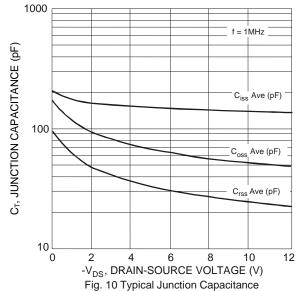


Fig. 11 Gate Charge Characteristics







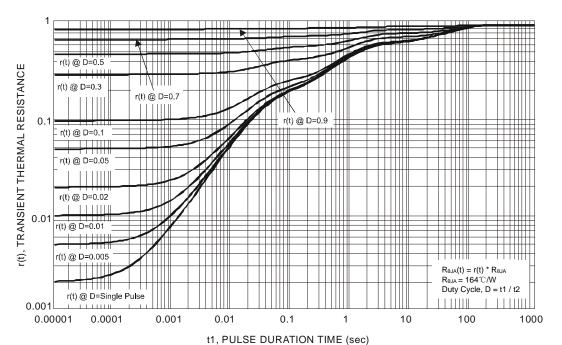


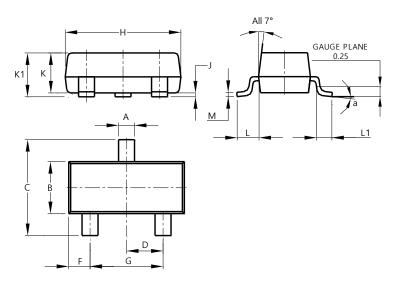
Fig. 12 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

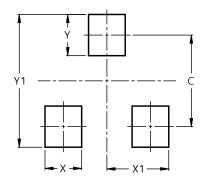


	SOT23								
Dim	Min	Max	Тур						
Α	0.37	0.51	0.40						
В	1.20	1.40	1.30						
С	2.30	2.50	2.40						
D	0.89	1.03	0.915						
F	0.45	0.60	0.535						
G	1.78	2.05	1.83						
Н	2.80	3.00	2.90						
J	0.013	0.10	0.05						
K	0.890	1.00	0.975						
K1	0.903	1.10	1.025						
L	0.45	0.61	0.55						
L1	0.25	0.55	0.40						
M	0.085	0.150	0.110						
а	0°	8°							
All Dimensions in mm									

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)			
С	2.0			
Х	0.8			
X1	1.35			
Y	0.9			
V1	2.0			



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